

/ Descriptions

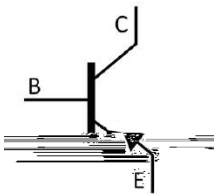
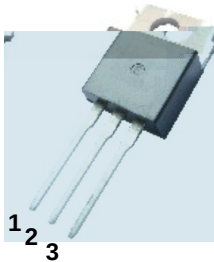
Silicon PNP transistor in a TO-220 Plastic Package.

/ Features

Complement to 2N6123.

/ Applications

Medium power linear switching applications.

/ Equivalent Circuit**/ Pinning**

PIN1 Base PIN 2 Collector PIN 3 Emitter

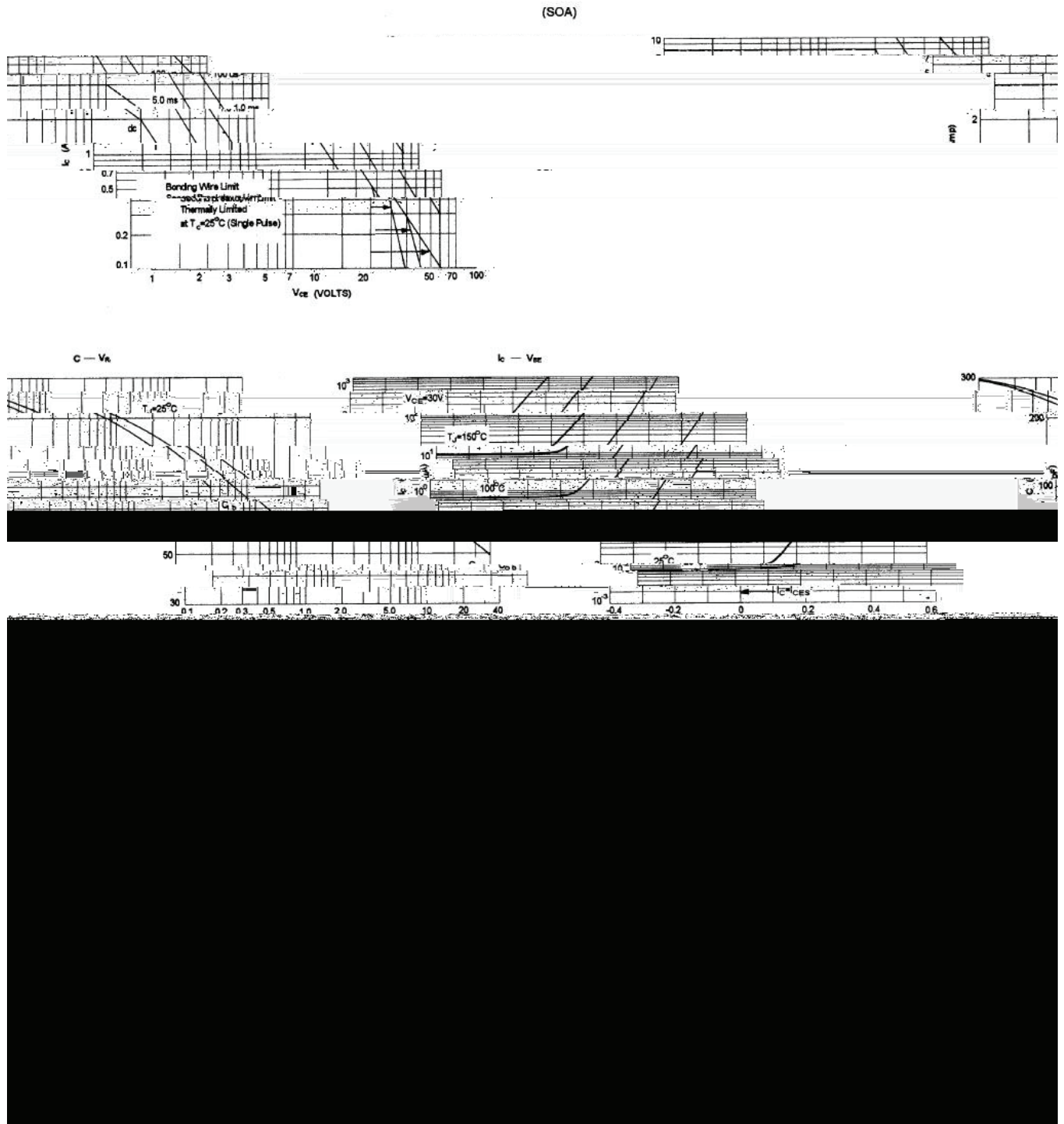
/ h_{FE} Classifications & Marking

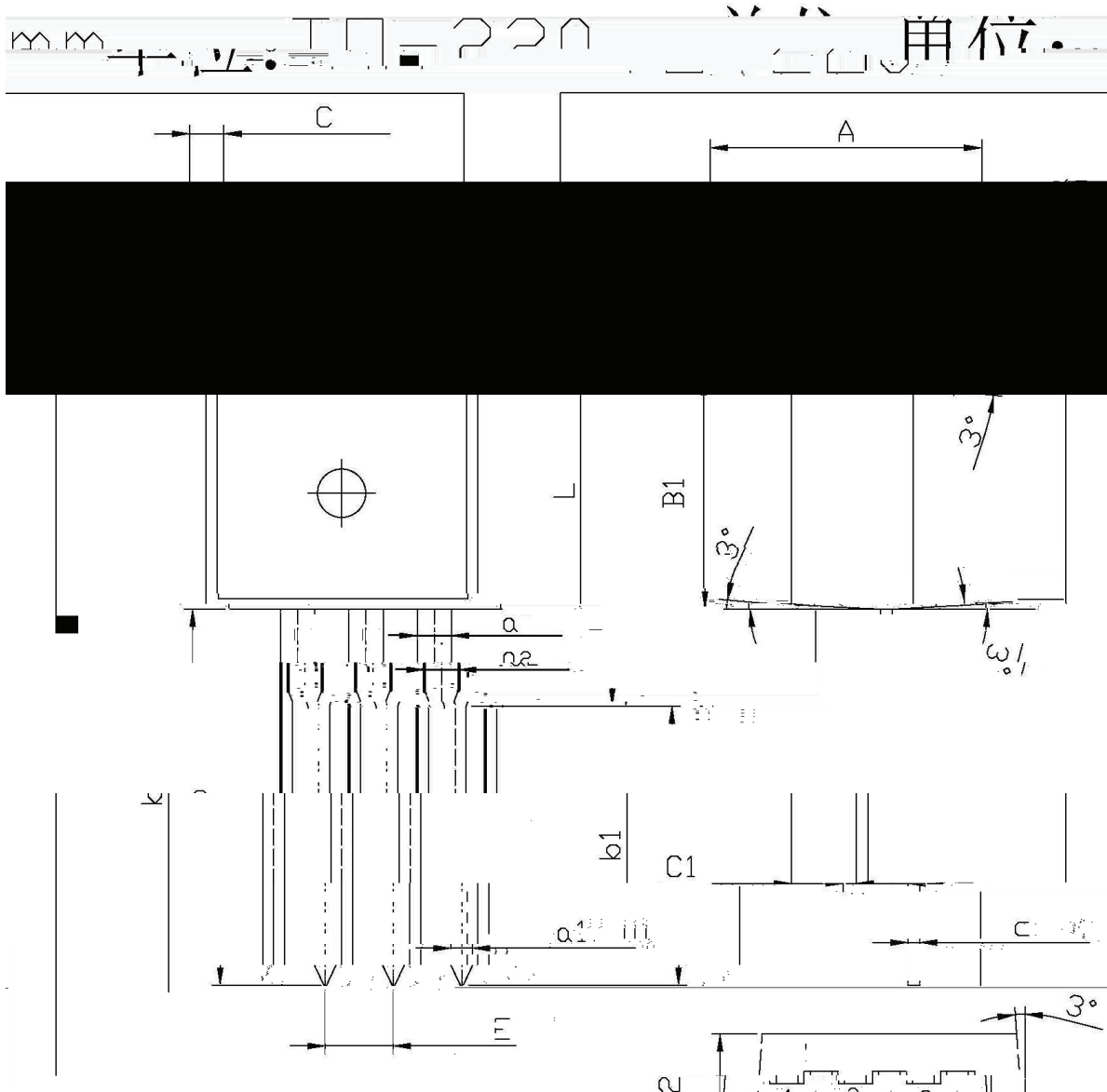
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-4.0	A
Peak Collector Current	I_{CM}	-7.0	A
Base Current - Continuous	I_B	-1.0	A
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	40	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage*	$*V_{CEO}$	$I_C=-100\text{mA}$ $I_B=0$	-80			V
Collector to Emitter Breakdown Voltage	V_{CBO}	$I_C=-1\text{mA}$ $I_E=0$	-80			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-1\text{mA}$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-80\text{V}$ $I_E=0$			-0.1	mA

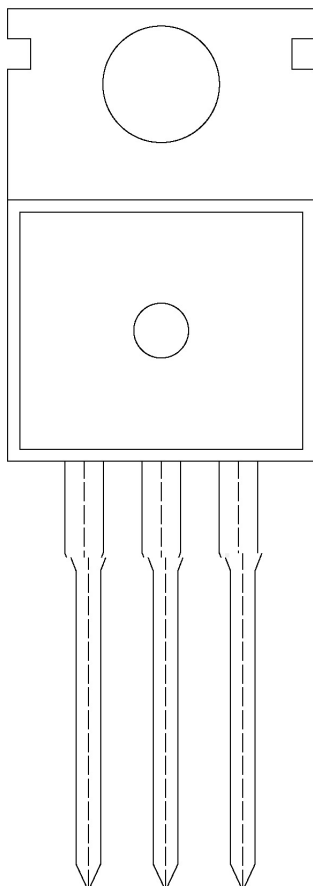
/ Electrical Characteristic Curve





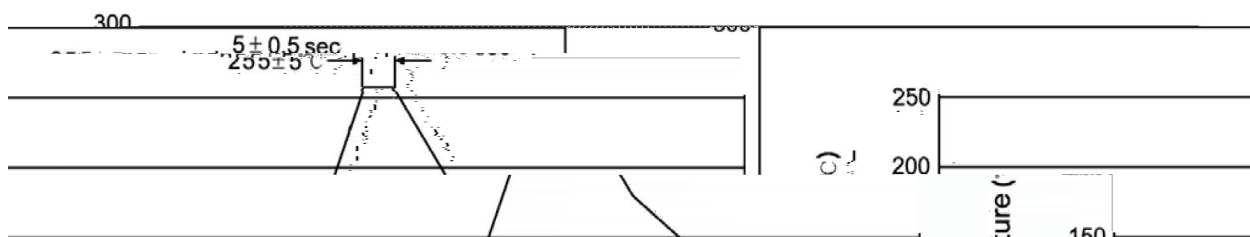
Dimensions in Millimeters			Dimensions in Millimeters		
Symbol	Min	Max	Symbol	Min	Max
Δ	9.8	10.2	C	12	14
R	3.56	3.64	R	15.7	16.1
C1	2.2	2.6	b	12.6	13.6

/ Marking Instructions



BR

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-----|-----|----|---------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255 | 5 | 5 | 0.5sec; | 2.Peak Temp.:255 5 , Duration:5 0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量			Dimension 包装尺寸 (unit: mm ³)
	只 套管	套管 盒	只 盒	